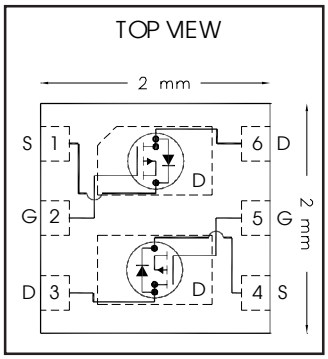
International
IOR Rectifier

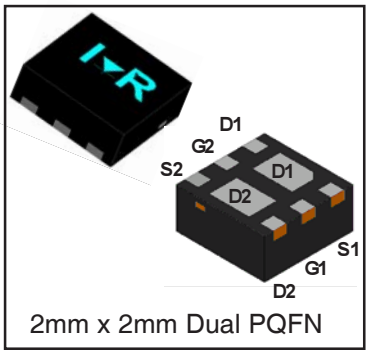
PD - 97572A

IRFHS9351PbF

HEXFET® Power MOSFET

V_{DS}	-30	V
$V_{GS\ max}$	±20	V
$R_{DS(on)\ max}$ (@V_{GS} = -10V)	170	mΩ
I_D (@T_C = 25°C)	-3.4②	A





2mm x 2mm Dual PQFN

Applications

- Charge and Discharge Switch for Battery Application
- System/load switch

Features and Benefits

Features		Benefits
Low R_{DSon} (≤ 170mΩ)		Lower Conduction Losses
Low Thermal Resistance to PCB (≤ 19°C/W)		Enable better thermal dissipation
Low Profile (≤ 1.0 mm)	results in	Increased Power Density
Compatible with Existing Surface Mount Techniques		Easier Manufacturing
RoHS Compliant Containing no Lead, no Bromide and no Halogen		Environmentally Friendlier
MSL1, Consumer Qualification		Increased Reliability

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRFHS9351TRPBF	PQFN 2mm x 2mm	Tape and Reel	4000	
IRFHS9351TR2PBF	PQFN 2mm x 2mm	Tape and Reel	400	

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	-30	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ -10V	-2.3	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ -10V	-1.5	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ -10V	-5.1②	
I_D @ T_C = 70°C	Continuous Drain Current, V_{GS} @ -10V	-4.1②	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Package Limited)	-3.4②	
I_{DM}	Pulsed Drain Current ①	-20	
P_D @T_A = 25°C	Power Dissipation ④	1.4	W
P_D @ T_A = 70°C	Power Dissipation ④	0.9	
	Linear Derating Factor	0.01	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Notes ① through ⑥ are on page 2

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	-30	—	—	V	V_{GS} = 0V, I_D = -250µA
$V_{DSS}/\ T_J$	Breakdown Voltage Temp. Coefficient	—	0.02	—	V/°C	Reference to 25°C, I_D = -1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	135	170	m	V_{GS} = -10V, I_D = -3.1A ③
		—	235	290		V_{GS} = -4.5V, I_D = -2.5A ③
$V_{GS(th)}$	Gate Threshold Voltage	-1.3	-1.8	-2.4	V	V_{DS} = V_{GS}, I_D = -10µA
$V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-4.6	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	µA	V_{DS} = -24V, V_{GS} = 0V
		—	—	-150		V_{DS} = -24V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V_{GS} = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V_{GS} = 20V
gfs	Forward Transconductance	2.4	—	—	S	V_{DS} = -10V, I_D = -3.1A
Q_g	Total Gate Charge ⑥	—	1.9	—	nC	V_{DS} = -15V, V_{GS} = -4.5V, I_D = - 3.1A
Q_g	Total Gate Charge ⑥	—	3.7	—	nC	V_{GS} = -10V
Q_{gs}	Gate-to-Source Charge ⑥	—	0.6	—		V_{DS} = -15V
Q_{gd}	Gate-to-Drain Charge ⑥	—	1.1	—		I_D = -3.1A
R_G	Gate Resistance ⑥	—	17	—		
$t_{d(on)}$	Turn-On Delay Time	—	8.3	—	ns	V_{DD} = -15V, V_{GS} = -4.5V ③
t_r	Rise Time	—	30	—		I_D = -3.1A
$t_{d(off)}$	Turn-Off Delay Time	—	6.3	—		R_G = 1.8
t_f	Fall Time	—	7.9	—		See Figs. 19a & 19b
C_{iss}	Input Capacitance	—	160	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	39	—		V_{DS} = -25V
C_{rss}	Reverse Transfer Capacitance	—	26	—		f = 1.0KHz

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-5.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-20		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	T_J = 25°C, I_S = -3.1A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	—	20	30	ns	T_J = 25°C, I_F = -3.1A, V_{DD} = -15V
Q_{rr}	Reverse Recovery Charge	—	42	63	nC	di/dt = 370/µs ③

Thermal Resistance

	Parameter	Typ.	Max.	Units
R_{JC} (Bottom)	Junction-to-Case ⑤	—	19	°C/W
R_{JC} (Top)	Junction-to-Case ⑤	—	170	
R_{JA}	Junction-to-Ambient ④		90	
R_{JA}	Junction-to-Ambient (t<10s) ④	—	75	

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Current limited by package. .

③ Pulse width ≤ 400µs; duty cycle ≤ 2%.

④ When mounted on 1 inch square copper board.

⑤ R_θ is measured at T_J of approximately 90°C.

⑥ For DESIGN AID ONLY, not subject to production testing.

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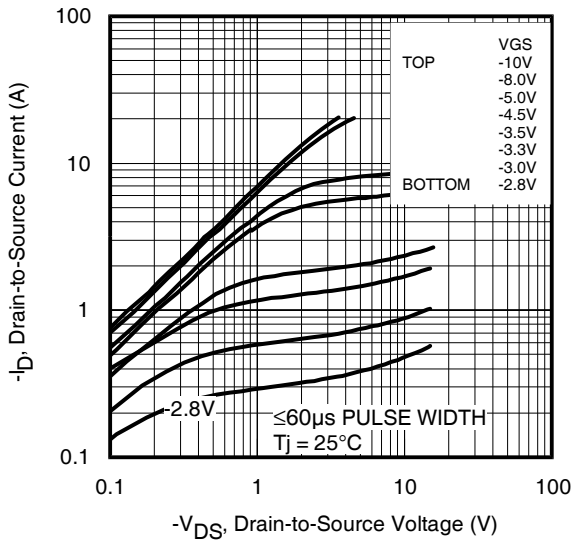


Fig 1. Typical Output Characteristics

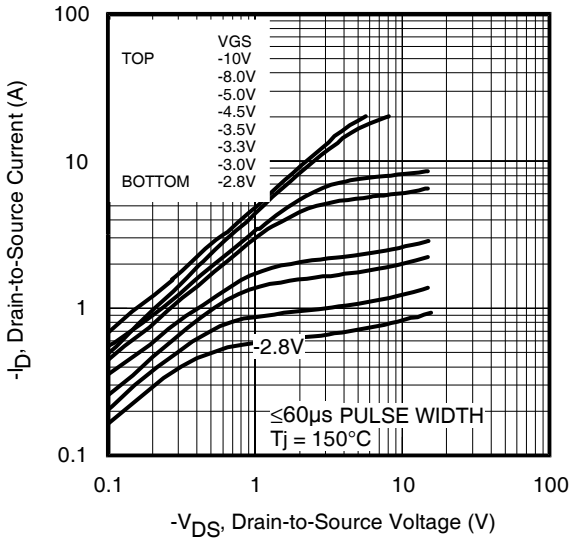


Fig 2. Typical Output Characteristics

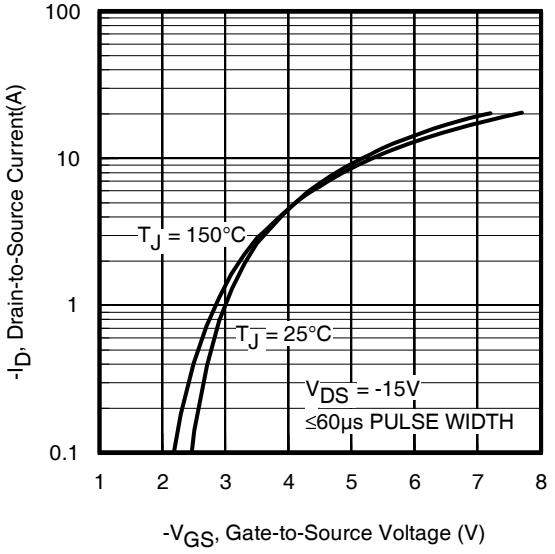


Fig 3. Typical Transfer Characteristics

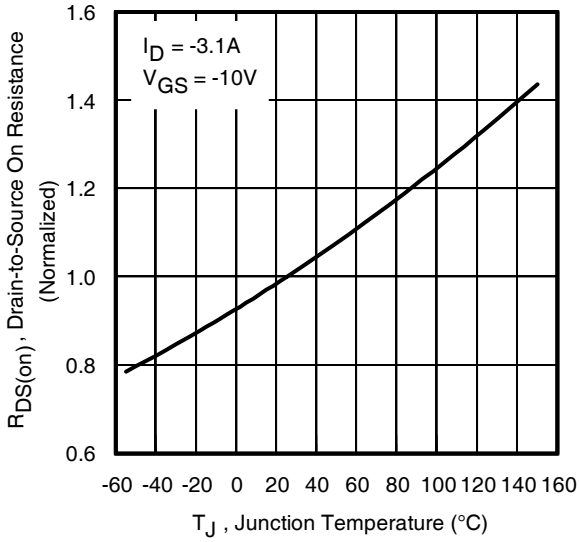


Fig 4. Normalized On-Resistance vs. Temperature

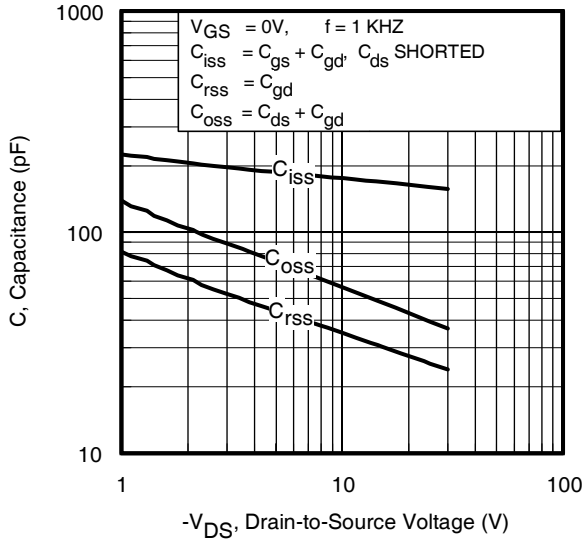


Fig 5. Typical Capacitance vs.Drain-to-Source Voltage

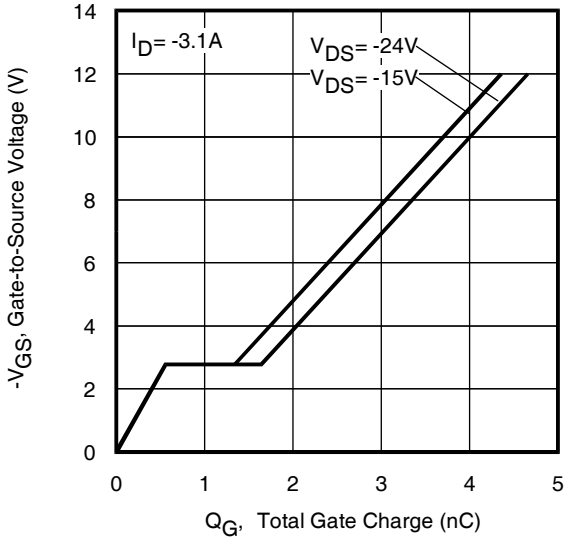


Fig 6. Typical Gate Charge vs.Gate-to-Source Voltage

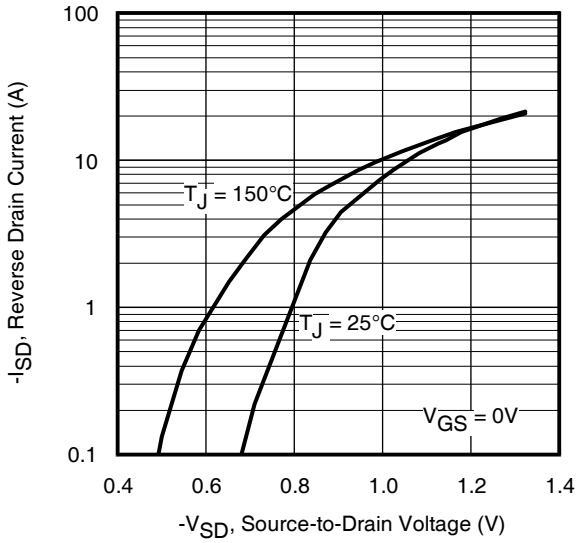


Fig 7. Typical Source-Drain Diode Forward Voltage

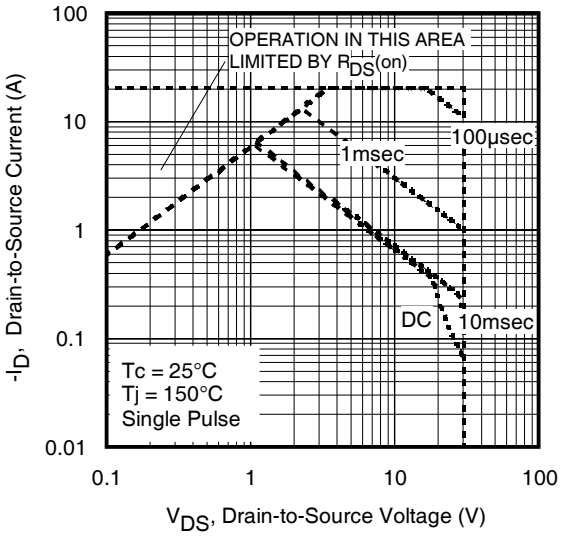


Fig 8. Maximum Safe Operating Area

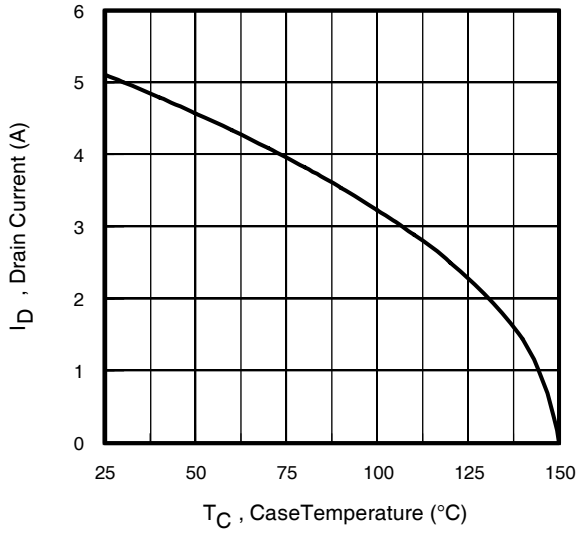


Fig 9. Maximum Drain Current vs. Case Temperature

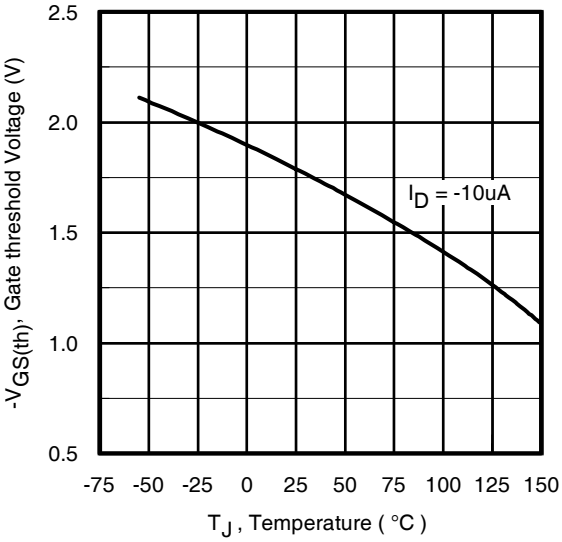


Fig 10. Threshold Voltage vs. Temperature

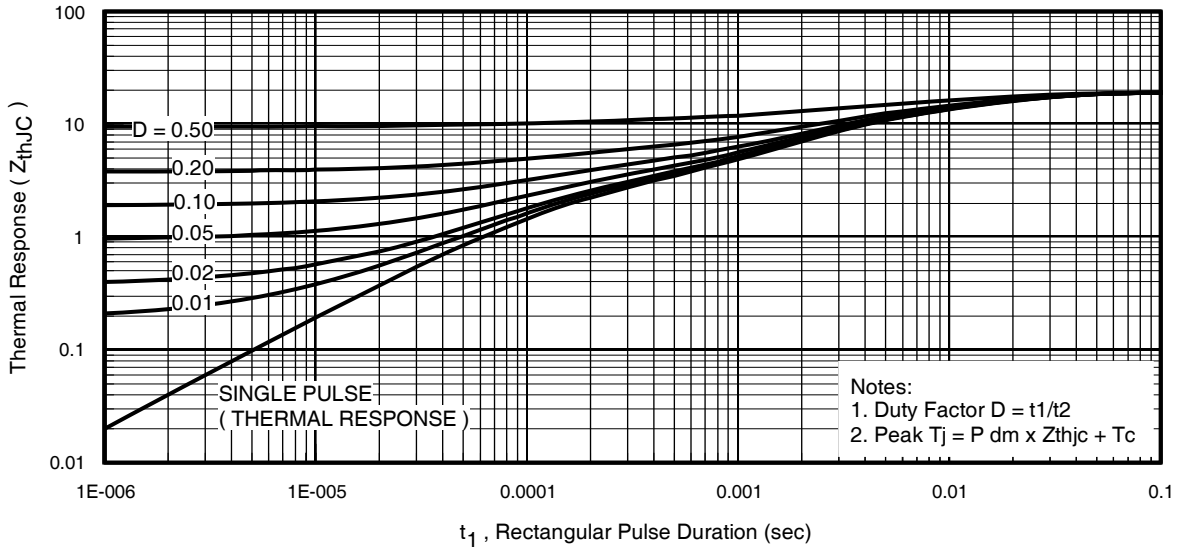


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

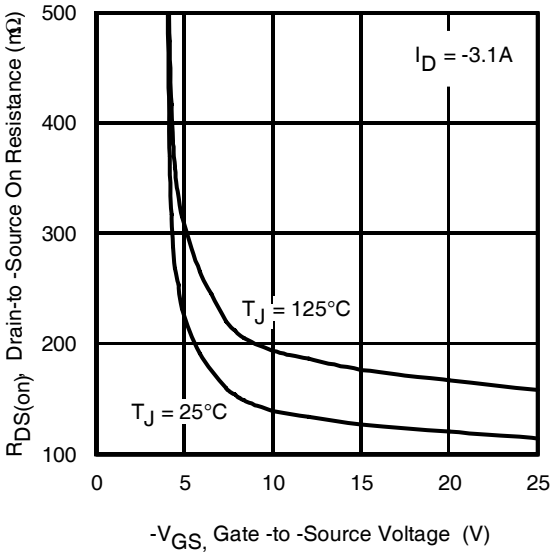


Fig 12. On-Resistance vs. Gate Voltage

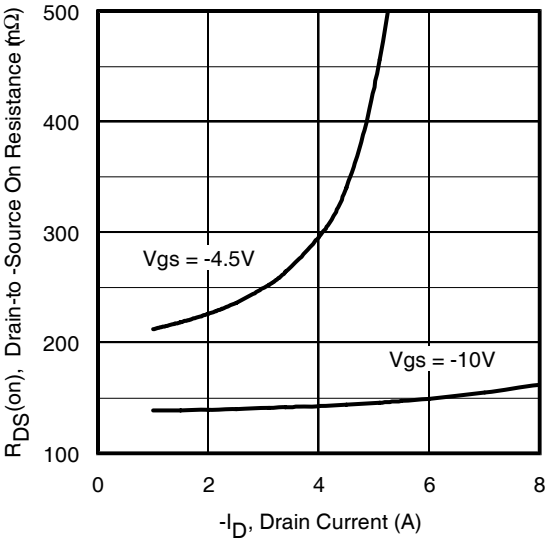


Fig 13. Typical On-Resistance vs. Drain Current

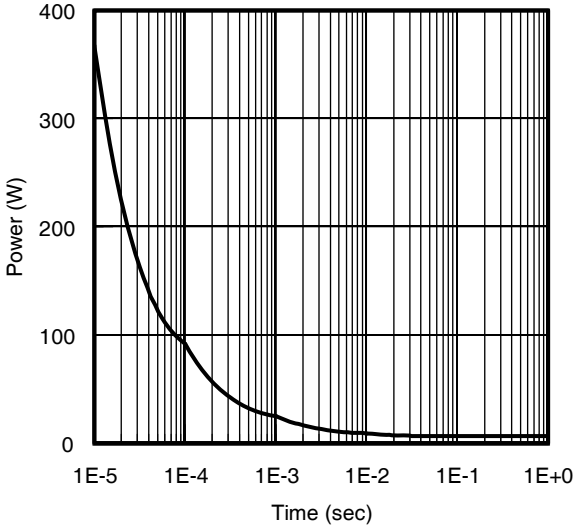
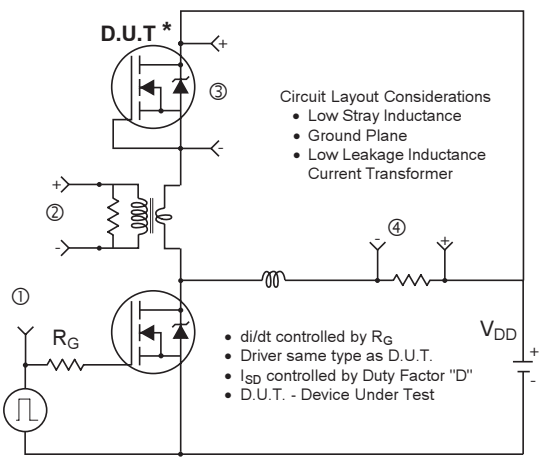
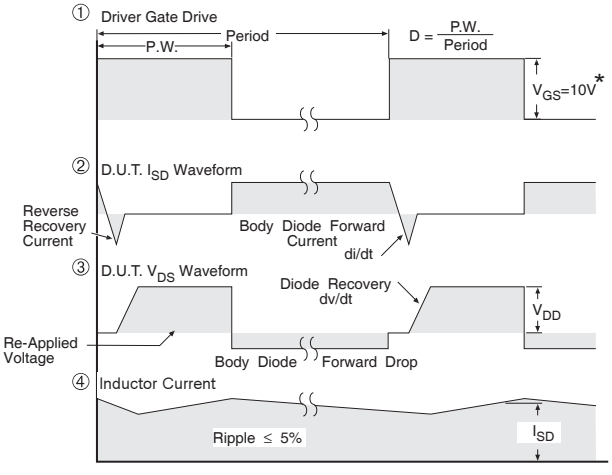


Fig 14. Typical Power vs. Time



* Reverse Polarity of D.U.T for P-Channel



* V_{GS} = 5V for Logic Level Devices

Fig 15. Diode Reverse Recovery Test Circuit for P-Channel HEXFET® Power MOSFETs

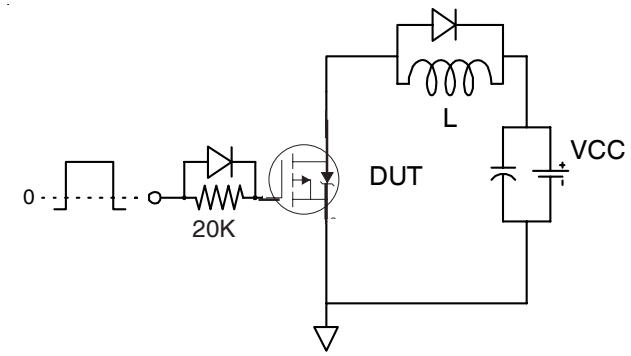


Fig 16a. Gate Charge Test Circuit

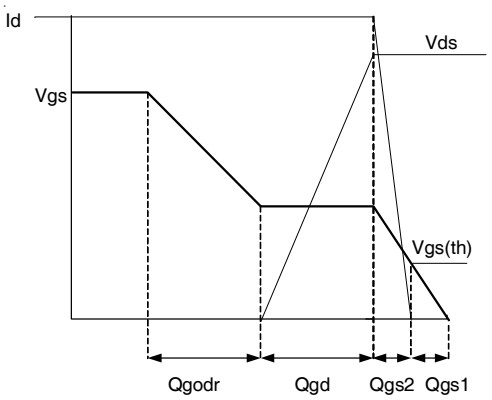


Fig 16b. Gate Charge Waveform

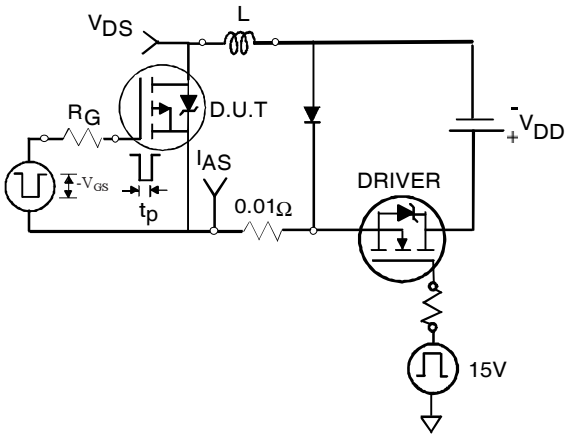


Fig 17a. Unclamped Inductive Test Circuit

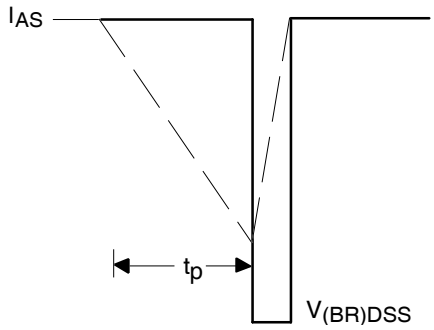


Fig 17b. Unclamped Inductive Waveforms

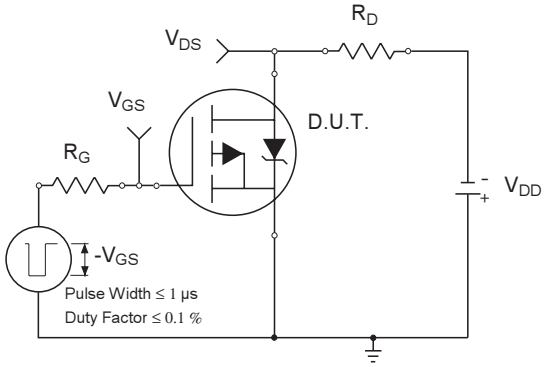


Fig 18a. Switching Time Test Circuit

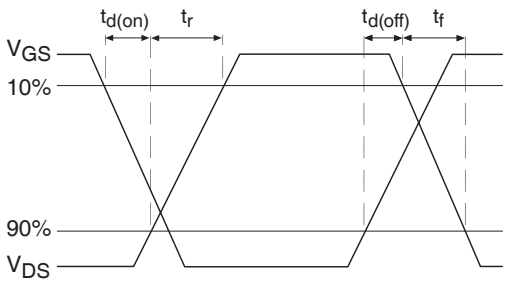
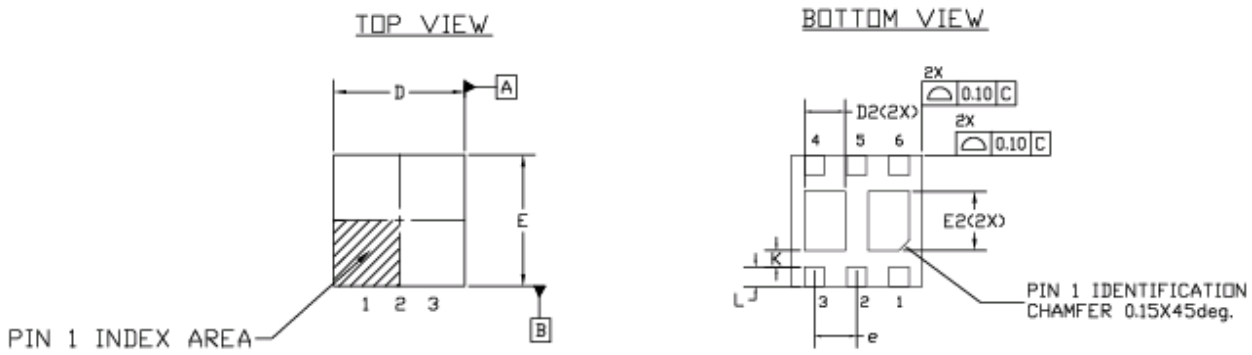
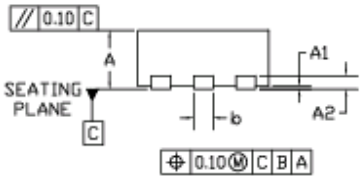


Fig 18b. Switching Time Waveforms

PQFN Package Details



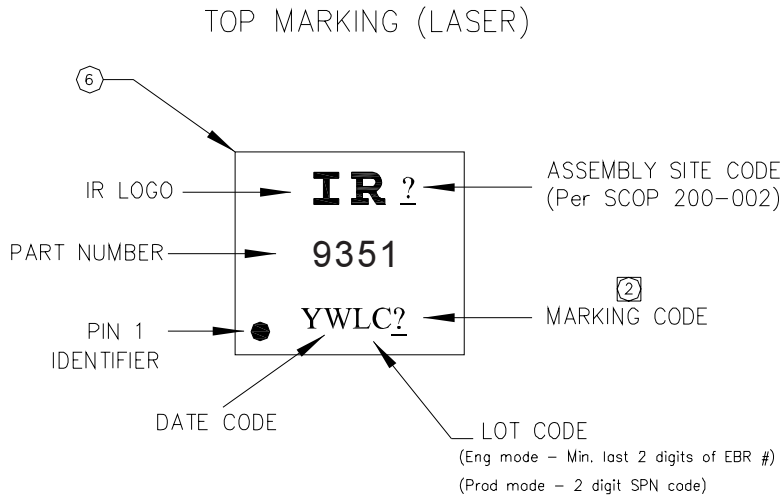


SYMBOL	COMMON					
	DIMENSIONS MILLIMETER			DIMENSIONS INCH		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.036	0.040
A1	0.00	0.02	0.05	0.000	0.001	0.002
A2	0.203 REF			0.008 REF		
b	0.25	0.30	0.35	0.010	0.012	0.014
D	1.90	2.00	2.10	0.075	0.079	0.083
D2	0.575	0.625	0.675	0.023	0.025	0.027
E	1.90	2.00	2.10	0.075	0.079	0.083
E2	0.85	0.90	0.95	0.034	0.036	0.038
e	0.65 BSC			0.026 BSC		
L	0.25	0.30	0.35	0.010	0.012	0.014
K	0.25	–	–	0.010	–	–

NOTES :

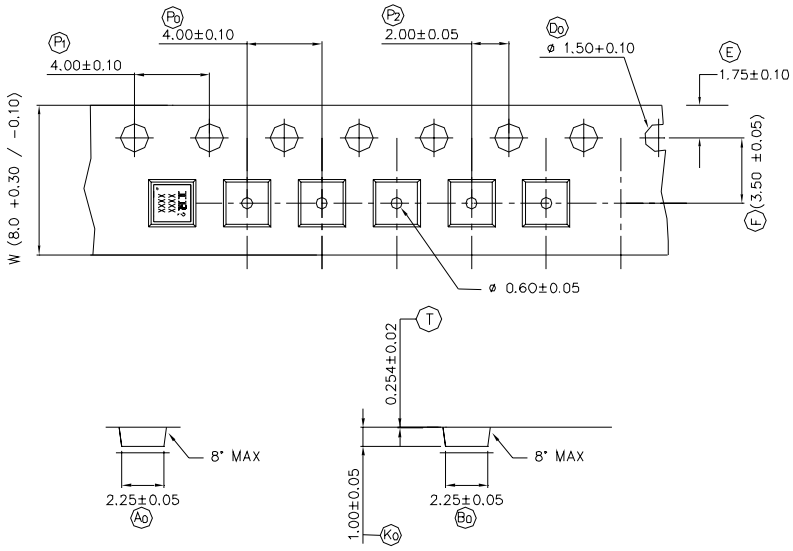
1. DIMENSION AND TOLERANCING CONFORM TO ASME Y14.5M-1994.
2. CONTROLLING DIMENSIONS : MILLIMETER. CONVERTED INCH DIMENSION ARE NOT NECESSARILY EXACT.

PQFN Part Marking



Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

PQFN Tape and Reel



NOTE: The Surface Resistivity is 10^{4} – 10^{8} OHM/SQ

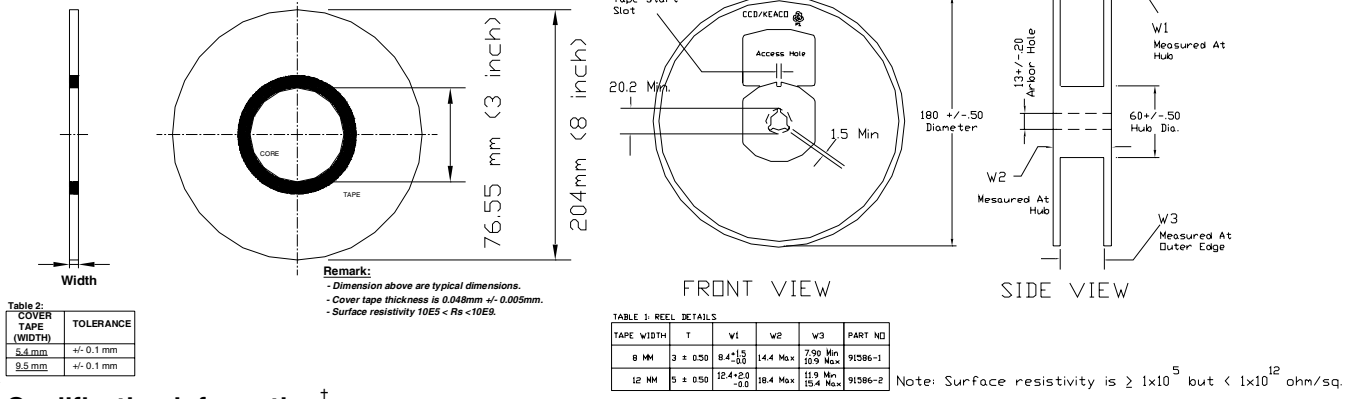


Table 2:

COVER TAPE (WIDTH)	TOLERANCE
5.4 mm	+/- 0.1 mm
9.5 mm	+/- 0.1 mm

Remark:
- *Dimension above are typical dimensions.*
- *Cover tape thickness is 0.048mm +/- 0.005mm.*
- *Surface resistivity 10E5 < Rs <10E9.*

TABLE 1: REEL DETAILS

TAPE WIDTH	T	W1	W2	W3	PART NO
8 MM	3 ± 0.50	8.4 +1.5 −0.0	14.4 Max	7.90 Min 10.9 Max	91586-1
12 MM	5 ± 0.50	12.4 +2.0 −0.0	18.4 Max	11.9 Min 15.4 Max	91586-2

Note: Surface resistivity is ≥ $1x10^{5}$ but < $1x10^{12}$ ohm/sq.

Qualification information†

Qualification level	Consumer†† (per JEDEC JESD47F ††† guidelines)	
Moisture Sensitivity Level	PQFN 2mm x 2mm	MSL1 (per IPC/JEDEC J-STD-020D†††)
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site http://www.irf.com/product-info/reliability

†† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information: http://www.irf.com/whoto-call/salesrep/

††† Applicable version of JEDEC standard at the time of product release.

Data and specifications subject to change without notice.

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